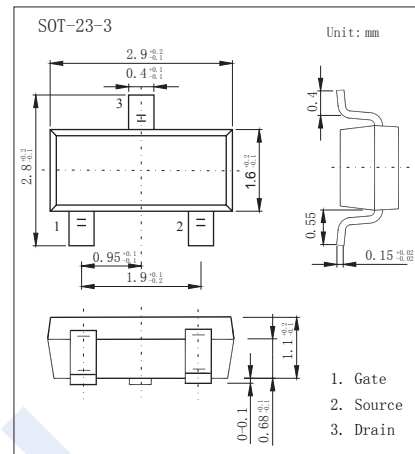
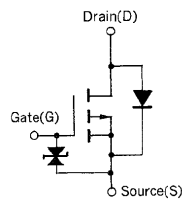


P-Channel MOSFET

2SJ203

■ Features

- $V_{DS} (V) \approx -16V$
- $I_D \approx -200mA$
- $R_{DS(ON)} < 23\Omega$ ($V_{GS} \approx -2.5V$)
- $R_{DS(ON)} < 10\Omega$ ($V_{GS} \approx -4V$)



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-16	V
Gate-Source Voltage	V_{GS}	± 7	
Continuous Drain Current	I_D	-200	mA
Pulsed Drain Current (Note.1)	I_{DM}	-400	
Power Dissipation	P_D	200	mW
Junction Temperature	T_J	150	$^\circ C$
Operating Temperature	T_{opt}	-55 to 80	
Junction Storage Temperature Range	T_{stg}	-55 to 150	

Note.1: $PW \leq 10ms$, Duty Cycle $\leq 50\%$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$I_D = -250\mu A$, $V_{GS} = 0V$	-16			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -16V$, $V_{GS} = 0V$			-1	μA
Gate-Body leakage current	I_{GSS}	$V_{DS} = 0V$, $V_{GS} = \pm 3V$			± 10	μA
Gate Cut off Voltage	$V_{GS(off)}$	$V_{DS} = -3V$, $I_D = -1\mu A$	-1.2		-2.2	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -2.5V$, $I_D = -1mA$			23	Ω
		$V_{GS} = -4V$, $I_D = -1mA$			10	
Forward Transconductance	g_{FS}	$V_{DS} = -3V$, $I_D = -10mA$	20	48		mS
Input Capacitance	C_{iss}	$V_{GS} = 0V$, $V_{DS} = -3V$, $f = 1MHz$		28		pF
Output Capacitance	C_{oss}			32		
Reverse Transfer Capacitance	C_{rss}			6		
Turn-On DelayTime	$t_{d(on)}$	$V_{GS(on)} = -3V$, $V_{DS} = -3V$, $I_D = -10mA$, $R_L = 300\Omega$, $R_{GEN} = 10\Omega$		180		ns
Turn-On Rise Time	t_r			420		
Turn-Off DelayTime	$t_{d(off)}$			100		
Turn-Off Fall Time	t_f			200		

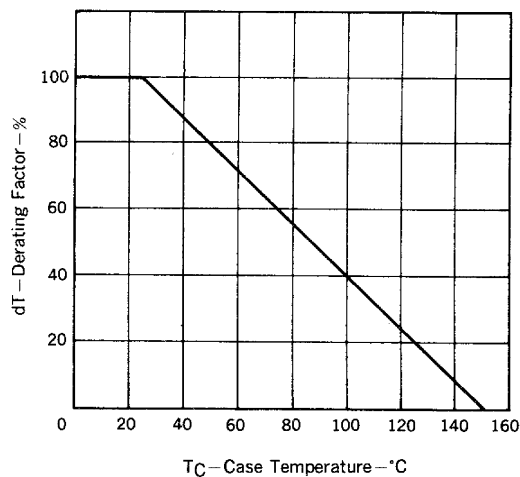
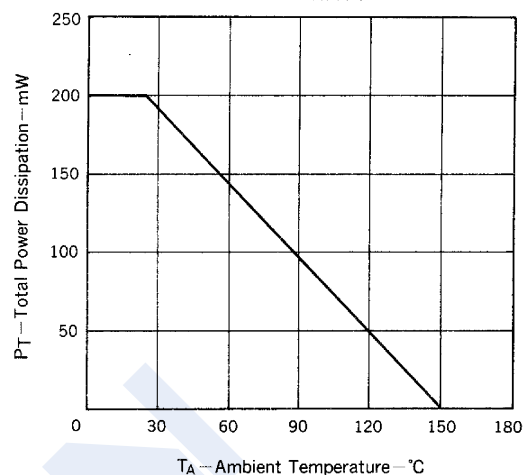
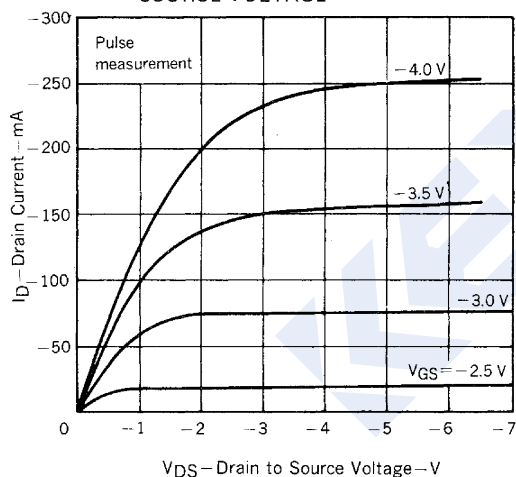
■ Marking

Marking	H14
---------	-----

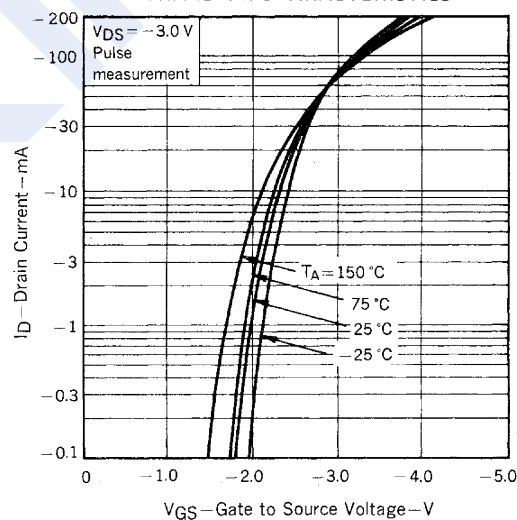
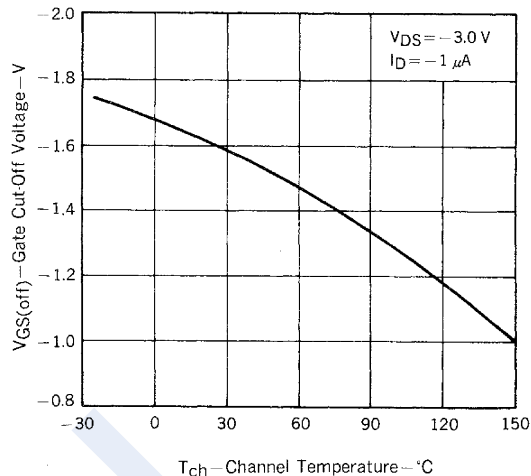
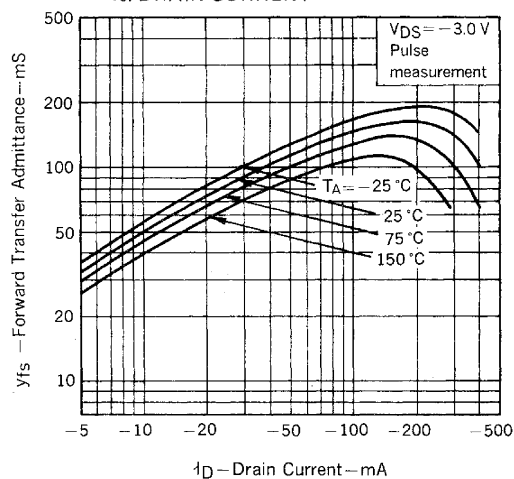
P-Channel MOSFET

2SJ203

■ Typical Characteristics

DERATING FACTOR OF FORWARD BIAS
SAFE OPERATING AREATOTAL POWER DISSIPATION vs.
AMBIENT TEMPERATUREDRAIN CURRENT vs. DRAIN TO
SOURCE VOLTAGE

TRANSFER CHARACTERISTICS

GATE TO SOURCE CUTOFF VOLTAGE
vs. CHANNEL TEMPERATUREFORWARD TRANSFER ADMITTANCE
vs. DRAIN CURRENT

P-Channel MOSFET

2SJ203

■ Typical Characteristics

